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# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









#### SINGLE 2 INPUT POSITIVE NAND GATE

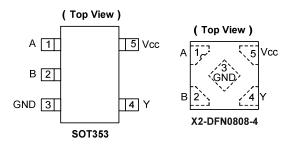
#### **Description**

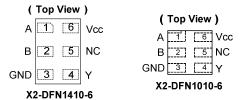
The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

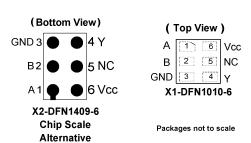
The 74AUP1G00 is a single two-input positive NAND gate with a standard push-pull output designed for operation over a power supply range of 0.8V to 3.6V. The device is fully specified for partial power down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

$$Y = \overline{A \bullet B}$$
 or  $Y = \overline{A} + \overline{B}$ 

#### **Pin Assignments**







#### **Features**

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- ±4 mA Output Drive at 3.0V
- Low Static Power Consumption

 $I_{CC} < 0.9 \mu A$ 

• Low Dynamic Power Consumption

C<sub>PD</sub> = 6pF (Typical at 3.6V)

- Schmitt Trigger Action at all inputs makes the circuit tolerant for slower input rise and fall time. The hysteresis is typically 250mV at  $V_{CC} = 3.0V$ .
- I<sub>OFF</sub> Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22

2000-V Human Body Model (A114)

Exceeds 1000-V Charged Device Model (C101)

- Latch-Up Exceeds 100mA per JESD 78, Class I
- Leadless Packages Named per JESD30E
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

# **Applications**

- Suited for Battery and Low Power Needs
- Wide array of products such as:
  - Tablets, E-readers
  - Cell Phones, Personal Navigation / GPS
  - MP3 Players ,Cameras, Video Recorders
  - PCs, Ultrabooks, Notebooks, Netbooks
  - Computer Peripherals, Hard Drives, SSDs, CD/DVD ROMs
  - TVs, DVDs, DVRs, Set-Top Boxes

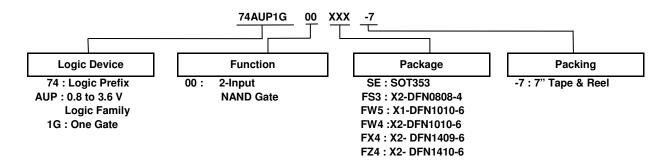
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



#### **Ordering Information**



Device	Package	Package	Package	7" Tape	and Reel
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix
74AUP1G00SE-7	SE	SOT353	2.0mm x 2.0mm x 1.1mm 0.65 mm lead pitch	3,000/Tape & Reel	-7
74AUP1G00FS3-7	FS3	X2-DFN0808-4	0.8mm x 0.8mm x 0.35mm 0.5 mm pad pitch (diamond)	5,000/Tape & Reel	-7
74AUP1G00FW5-7	FW5	X1-DFN1010-6	1.0mm x 1.0mm x 0.5mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FW4-7	FW4	X2-DFN1010-6	1.0mm x 1.0mm x 0.4mm 0.35 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FX4-7	FX4	X2-DFN1409-6 Chip Scale Alternative	1.4mm x 0.9mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7
74AUP1G00FZ4-7	FZ4	X2-DFN1410-6	1.4mm x 1.0mm x 0.4mm 0.5 mm pad pitch	5,000/Tape & Reel	-7

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

#### **Pin Descriptions**

Pin Name	Function
Α	Data Input
В	Data Input
GND	Ground
Y	Data Output
V <sub>CC</sub>	Supply Voltage

#### **Logic Diagram**



#### **Function Table**

Inp	uts	Output
Α	В	Υ
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

<sup>5.</sup> The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.



### Absolute Maximum Ratings (Notes 6 & 7) (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V <sub>CC</sub>	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < 0	50	mA
l <sub>OK</sub>	Output Clamp Current (V <sub>O</sub> < 0 )	50	mA
lo	Continuous Output Current (V <sub>O</sub> = 0 to V <sub>CC</sub> )	±20	mA
I <sub>CC</sub>	Continuous Current Through V <sub>CC</sub>	50	mA
I <sub>GND</sub>	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	℃
T <sub>STG</sub>	Storage Temperature	-65 to +150	℃

Notes:

#### Recommended Operating Conditions (Note 8) (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Symbol	Pi	arameter	Min	Max	Unit
V <sub>CC</sub>	Operating Voltage		0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 0.8V	_	-20	μΑ
		V <sub>CC</sub> = 1.1V	_	-1.1	
	High Lavel Output Current	V <sub>CC</sub> = 1.4V	_	-1.7	
I <sub>OH</sub>	High-Level Output Current	V <sub>CC</sub> = 1.65V	_	-1.9	mA
		V <sub>CC</sub> = 2.3V	_	-3.1	
		V <sub>CC</sub> = 3.0V	_	-4	
		V <sub>CC</sub> = 0.8V	_	20	μΑ
		V <sub>CC</sub> = 1.1V	_	1.1	
	Low-Level Output Current	V <sub>CC</sub> = 1.4V	_	1.7	
l <sub>OL</sub>	Low-Level Output Current	V <sub>CC</sub> = 1.65V	_	1.9	mA
		V <sub>CC</sub> = 2.3V	_	3.1	
		V <sub>CC</sub> = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V <sub>CC</sub> = 0.8V to 3.6V	_	200	ns/V
TA	Operating Free-Air Temperature		-40	125	℃

Note: 8. Unused inputs should be held at  $V_{CC}$  or Ground.

<sup>6.</sup> Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

<sup>7.</sup> Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



## **Electrical Characteristics** (@T<sub>A</sub> = +25 ℃, unless otherwise specified.)

Cumabal	Downwater	Took Conditions		T <sub>A</sub> = -	+25°C	T <sub>A</sub> = -40 ℃	C to +85°C	Unit
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 x V <sub>CC</sub>	_	0.80 x V <sub>CC</sub>	_	
.,,	High-Level Input	_	1.65V to 1.95V	0.65 x V <sub>CC</sub>	_	0.65 x V <sub>CC</sub>	_	v
V <sub>IH</sub>	Voltage	_	2.3V to 2.7V	1.6	_	1.6	_	·
		_	3.0V to 3.6V	2.0	_	2.0	_	
		_	0.8V to 1.65V	_	0.30 x V <sub>CC</sub>	_	0.30 x V <sub>CC</sub>	
V <sub>IL</sub>	Low-Level Input	_	1.65V to 1.95V	_	0.35 x V <sub>CC</sub>	_	0.35 x V <sub>CC</sub>	v
VIL	Voltage	_	2.3V to 2.7V	_	0.7	_	0.7	V
		_	3.0V to 3.6V	_	0.9	_	0.9	
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V <sub>CC</sub> - 0.1	_	V <sub>CC</sub> – 0.1	_	
		I <sub>OH</sub> = -1.1mA	1.1V	0.75 x V <sub>CC</sub>	_	0.7 x V <sub>CC</sub>	_	
		I <sub>OH</sub> = -1.7mA	1.4V	1.11	_	1.03	_	
.,	High-Level Output	I <sub>OH</sub> = -1.9mA	1.65V	1.32	_	1.3	_	.,
V <sub>OH</sub>	Voltage	I <sub>OH</sub> = -2.3mA	0.01/	2.05	_	1.97	_	V
		I <sub>OH</sub> = -3.1mA	2.3V	1.9	_	1.85	_	
		I <sub>OH</sub> = -2.7mA	2)./	2.72	_	2.67	_	
		I <sub>OH</sub> = -4mA	- 3V	2.6	_	2.55	_	
		I <sub>OL</sub> = 20μA	0.8V to 3.6V	_	0.1	_	0.1	
		I <sub>OL</sub> = 1.1mA	1.1V	_	0.3 x V <sub>CC</sub>	_	0.3 x V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7mA	1.4V	_	0.31	_	0.37	
	Low-Level Output	I <sub>OL</sub> = 1.9mA	1.65V	_	0.31	_	0.35	
$V_{OL}$	Voltage	I <sub>OL</sub> = 2.3mA		_	0.31	_	0.33	V
		I <sub>OL</sub> = 3.1mA	2.3V	_	0.44	_	0.45	
		I <sub>OL</sub> = 2.7mA		_	0.31	_	0.33	
		I <sub>OL</sub> = 4mA	3V	_	0.44	_	0.45	
I <sub>1</sub>	Input Current	A or B Input V <sub>I</sub> = GND to 3.6V	0 to 3.6V	_	± 0.1	_	± 0.5	μΑ
loff	Power Down Leakage Current	$V_I$ or $V_O = 0V$ to 3.6V	0	_	0.2	_	0.6	μΑ
Δl <sub>OFF</sub>	Delta Power Down Leakage Current	$V_I$ or $V_O = 0V$ to 3.6V	0 V to 0.2V	_	0.2	_	0.6	μΑ
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8 V to 3.6V	_	0.5	_	0.9	μA
ΔI <sub>CC</sub>	Additional Supply Current	One Input at V <sub>CC</sub> -0.6V Other Inputs at V <sub>CC</sub> or GND	3.3V	_	40	_	50	μА



### **Electrical Characteristics** (continued) (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Cymphol	Parameter	Test Conditions	V	T <sub>A</sub> = -40 ℃	to +125℃	Unit	
Symbol	Parameter	rest Conditions	Vcc	Min	Max	Unit	
		_	0.8V to 1.65V	0.80 x V <sub>CC</sub>	_		
V <sub>IH</sub>	High-Level Input Voltage	_	1.65V to 1.95V	0.70 x V <sub>CC</sub>	_	V	
VIH	i ligh-Level input voltage	_	2.3V to 2.7V	1.6	_	v	
		_	3.0V to 3.6V	2.0	_		
		_	0.8V to 1.65V	_	0.25 x V <sub>CC</sub>		
$V_{IL}$	Low-Level Input Voltage	_	1.65V to 1.95V	_	0.30 x V <sub>CC</sub>	V	
V IL	Low-Level input voitage	_	2.3V to 2.7V	_	0.7	v	
		_	3.0V to 3.6V	_	0.9		
		$I_{OH} = -20\mu A$	0.8V to 3.6V	V <sub>CC</sub> - 0.11	_		
		I <sub>OH</sub> = -1.1mA	1.1V	0.6 x V <sub>CC</sub>	_		
		I <sub>OH</sub> = -1.7mA	1.4V	0.93	_		
.,	High Lavel Output Make se	I <sub>OH</sub> = -1.9mA	1.65V	1.17	_		
Voн	High-Level Output Voltage	I <sub>OH</sub> = -2.3mA	0.01/	1.77	_	V	
		I <sub>OH</sub> = -3.1mA	2.3V	1.67	_		
		I <sub>OH</sub> = -2.7mA	0)/	2.40	_		
		I <sub>OH</sub> = -4mA	3V	2.30	_		
		I <sub>OL</sub> = 20μA	0.8V to 3.6V		0.11		
		I <sub>OL</sub> = 1.1mA	1.1V	_	0.33 x V <sub>CC</sub>		
		I <sub>OL</sub> = 1.7mA	1.4V		0.41		
		I <sub>OL</sub> = 1.9mA	1.65V	_	0.39	.,	
V <sub>OL</sub>	Low-Level Output Voltage	I <sub>OL</sub> = 2.3mA	2.21/	_	0.36	V	
		I <sub>OL</sub> = 3.1mA	2.3V	_	0.50		
		I <sub>OL</sub> = 2.7mA		_	0.36		
		I <sub>OL</sub> = 4mA	3V		0.50		
II	Input Current	A or B Input, $V_I = GND$ to 3.6V	0 to 3.6V	_	± 0.75	μA	
l <sub>OFF</sub>	Power Down Leakage Current		0	_	± 3.5	μA	
Δl <sub>OFF</sub>	Delta Power Down Leakage Current	$V_1$ or $V_0 = 0V$ to 3.6V	0V to 0.2V	_	± 2.5	μA	
Icc	Supply Current	$V_I = GND \text{ or } V_{CC}, I_O = 0$	0.8V to 3.6V	_	3.0	μA	
Δl <sub>CC</sub>	Additional Supply Current	Input at V <sub>CC</sub> -0.6V Other Inputs at V <sub>CC</sub> or GND	3.3V	_	75	μΑ	



## **Switching Characteristics**

 $C_L = 5pF$ , See Figure 1

Parameter	From Input	TO OUTPUT	V	1	T <sub>A</sub> = +25°C		T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
Parameter			V <sub>cc</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	17.5	_	_	_	_	_	
		Y	1.2V ± 0.1V	2.5	5.3	11.0	2.1	12.2	2.1	13.5	
	A or B		1.5V ± 0.1V	2.0	3.8	6.8	1.8	7.8	1.8	8.6	
t <sub>pd</sub>	AOID		1.8V ± 0.15V	1.6	3.1	5.3	1.4	6.2	1.4	6.9	ns
			2.5V ± 0.2V	1.3	2.5	4.0	1.1	4.7	1.1	5.2	
			3.3V ± 0.3V	1.0	2.2	3.6	1.0	4.2	1.0	4.7	

C<sub>L</sub> = 10pF, See Figure 1

Parameter	From Input	TO OUTPUT	.,	1	T <sub>A</sub> = +25 ℃		T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
Farameter			Vcc	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	21.0	_	_	_	_	_	
			1.2V ± 0.1V	2.4	6.1	13.0	2.2	14.4	2.2	15.9	ns
	A or B	V	1.5V ± 0.1V	2.4	4.4	7.9	2.2	9.2	2.2	10.2	
t <sub>pd</sub>	AUID	Ť	1.8V ± 0.15V	2.0	3.7	6.2	1.9	7.3	1.9	8.1	
			2.5V ± 0.2V	1.4	3.0	4.7	1.3	5.6	1.3	6.2	
			$3.3V \pm 0.3V$	1.3	2.8	4.3	1.2	4.9	1.2	5.4	

C<sub>L</sub> = 15pF, See Figure 1

Parameter	From Input	TO OUTPUT	V	T <sub>A</sub> = +25 ℃			T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
Parameter			V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	24.5	_	_	_	_	_	
	A or B	Υ	1.2V ± 0.1V	3.4	6.9	14.8	3.1	16.5	3.1	18.2	ns
			1.5V ± 0.1V	2.8	5.0	8.9	2.5	10.5	2.5	11.6	
t <sub>pd</sub>			1.8V ± 0.15V	2.0	4.1	7.0	2.0	8.3	2.0	9.2	
			2.5V ± 0.2V	1.7	3.5	5.3	1.5	6.4	1.5	7.1	
			$3.3V \pm 0.3V$	1.6	3.2	4.9	1.4	5.7	1.4	6.3	

C<sub>L</sub> = 30pF, See Figure 1

Parameter	From Input	TO OUTPUT	V	T <sub>A</sub> = +25 ℃			T <sub>A</sub> = -40 °C to +85 °C		T <sub>A</sub> = -40 °C to +125 °C		Unit
raiailletei			V <sub>CC</sub>	Min	Тур	Max	Min	Max	Min	Max	Unit
			V8.0	_	34.8	_	_	_	_	_	
			1.2V ± 0.1V	4.6	17.5	22.0	4.1	22.6	4.1	24.9	ns
	A or B	V	1.5V ± 0.1V	3.0	6.5	11.8	2.9	14.0	2.9	15.4	
t <sub>pd</sub>	AOID	Y	1.8V ± 0.15V	2.6	5.4	9.3	2.3	11.1	2.3	12.3	
			2.5V ± 0.2V	2.4	4.6	7.1	2.1	8.5	2.1	9.4	
			3.3V ± 0.3V	2.3	2.6	6.5	2.1	7.6	2.1	8.4	



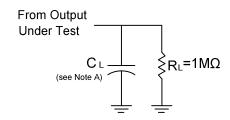
# Operating and Package Characteristics (@T<sub>A</sub> = +25 ℃, unless otherwise specified.)

	Parameter	Test Conditio	ons	V <sub>CC</sub>	Тур	Unit
				0.8V	6.5	
				1.2V ± 0.1V	6.3	
_	Power Dissipation	f = 1MH	lz	1.5V ± 0.1V	6.3	
$C_{pd}$	Capacitance	No Loa	d	1.8V ± 0.15V	6.2	pF
				2.5V ± 0.2V	6.2	
				3.3V ± 0.3V	6.1	
Ci	Input Capacitance	V <sub>i</sub> = V <sub>CC</sub> or	GND	0V or 3.3V	1.5	pF
		SOT353		_	371	
		X2-DFN0808-4	(Nata 0)	_	430	]
	Thermal Resistance	X1-DFN1010-6		_	435	00.444
$\theta_{\sf JA}$	Junction-to-Ambient	X2-DFN1010-6	(Note 9)	_	445	°C/W
		X2-DFN1409-6	1	_	470	
		X2-DFN1410-6	1	_	460	
		SOT353		_	143	
		X2-DFN0808-4	1	_	240	
	Thermal Resistance	X1-DFN1010-6	(NI-1- O)	_	250	00.444
θJC	Junction-to-Case	X2-DFN1010-6	(Note 9)	_	250	°C/W
		X2-DFN1409-6		_	275	
		X2-DFN1410-6	1	_	265	

Note: 9. Test condition for each of the six package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



#### **Parameter Measurement Information**



Vcc	Inputs		V	0
VCC	VI	t <sub>r</sub> /t <sub>f</sub>	$V_{M}$	CL
0.8V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
1.2V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
1.5V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
1.8V ±0.15V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
2.5V±0.2V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF
3.3V±0.3V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	5, 10, 15, 30pF

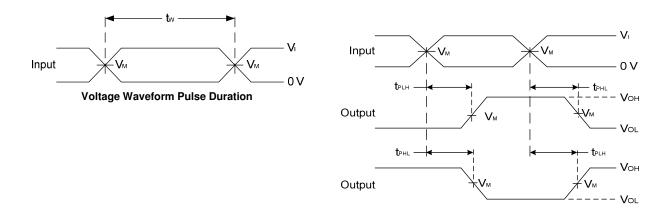


Figure 1 Load Circuit and Voltage Waveforms

**Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs** 

Notes: A. Includes test lead and test apparatus capacitance.

B. All pulses are supplied at pulse repetition rate ≤ 10MHz.

- C. Inputs are measured separately one transition per measurement.
- D. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>PD</sub>.



#### **Marking Information**

(1) SOT353

#### (Top View)

4 XX Y WX2 3 1

XX: Identification code

Y: Year 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents 52 and 53 week

 $\underline{X}$ : A $^{\sim}$ Z: Internal code

Part Number	Package	Identification Code	
74AUP1G00SE-7	SOT353	XH	

(2) X2-DFN0808-4, X1-DFN1010-6, X2-DFN1010-6, X2-DFN1409-6 and X2-DFN1410-6

(Top View)

XX $\underline{Y}\underline{W}\underline{X}$  XX: Identification Code

Y: Year: 0~9

 $\overline{\mathbf{W}}$ : Week: A~Z: 1~26 week;

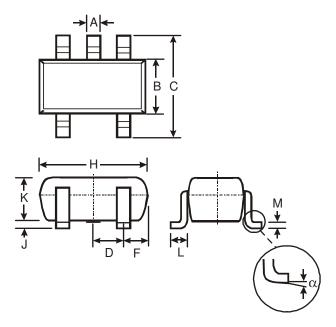
a~z: 27~52 week; z represents 52 and 53 week

X: A~Z: Internal code

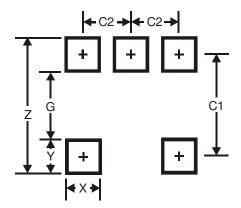
Part Number	Package	Identification Code
74AUP1G00FS3-7	X2-DFN0808-4	YJ
74AUP1G00FW5-7	X1-DFN1010-6	Q1
74AUP1G00FW4-7	X2-DFN1010-6	XH
74AUP1G00FX4-7	X2-DFN1409-6	HA
74AUP1G00FZ4-7	X2-DFN1410-6	XH



### SOT353 Package Outline Dimensions and Suggested Pad Layout



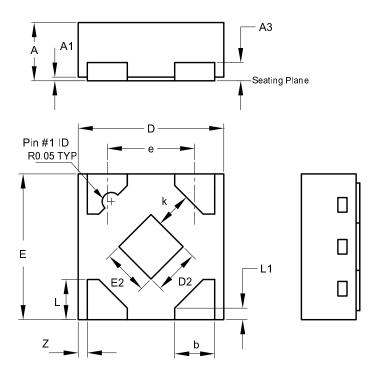
SOT353				
Dim	Min Max Typ			
Α	0.10	0.30	0.25	
В	1.15	1.35	1.30	
С	2.00	2.20	2.10	
D		0.65 Typ	)	
F	0.40	0.45	0.425	
Η	1.80	2.20	2.15	
7	0	0.10	0.05	
K	0.90	1.00	1.00	
L	0.25	0.40	0.30	
M	0.10	0.22	0.11	
α	0°	8°	-	
All Dimensions in mm				



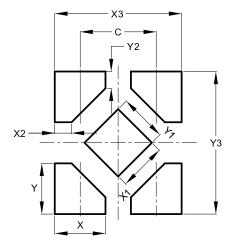
Dimensions	Value (in mm)	
Z	2.5	
G	1.3	
Х	0.42	
Υ	0.6	
C1	1.9	
C2	0.65	



### X2-DFN0808-4 Package Outline Dimensions and Suggested Pad Layout



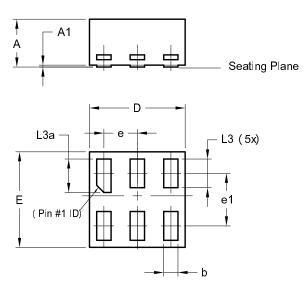
	X2-DFN0808-4				
Dim	Min	Max	Тур		
Α	0.25	0.35	0.30		
A1	0	0.04	0.02		
A3	-	-	0.13		
b	0.17	0.27	0.22		
D	0.75	0.85	0.80		
D2	0.15	0.35	0.25		
E	0.75	0.85	0.80		
E2	0.15	0.35	0.25		
е	-	-	0.48		
k	0.20	-	-		
L	0.17	0.27	0.22		
L1	0.02	0.12	0.07		
Z	-	-	0.05		
All Dimensions in mm					



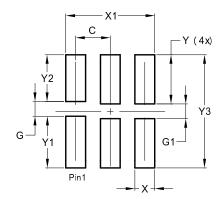
Dimensions	Value
С	0.480
X	0.320
X1	0.300
X2	0.106
Х3	0.800
Υ	0.320
<b>Y</b> 1	0.300
Y2	0.106
Y3	0.900



## X1-DFN1010-6 (Type B) Package Outline Dimensions and Suggested Pad Layout



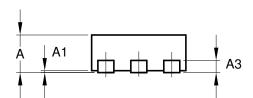
	X1-DFN1010-6 (Type B)				
Dim	` ' ' '				
Α	-	0.50	0.39		
A1	-	0.04	-		
b	0.12	0.20	0.15		
D	0.95	1.050	1.00		
Е	0.95	1.050	1.00		
е	0.35 BSC				
e1		0.55 BSC			
L3	0.27	0.30	0.30		
L3a	0.32	0.40	0.35		
All	All Dimensions in mm				

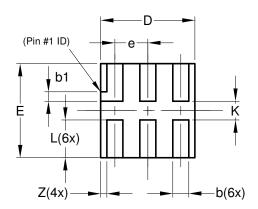


Dimensions	Value	
Dillielisions	(in mm)	
С	0.350	
G	0.150	
G1	0.150	
X	0.200	
X1	0.900	
Υ	0.500	
Y1	0.525	
Y2	0.475	
Y3	1.150	

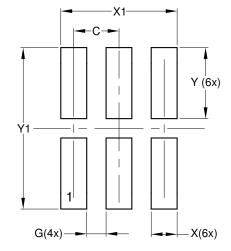


### X2-DFN1010-6 Package Outline Dimensions and Suggested Pad Layout





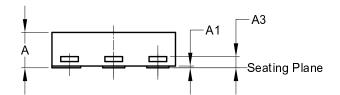
X2-DFN1010-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
<b>A</b> 1	0.00	0.05	0.02	
A3	_	_	0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
E	0.95	1.05	1.00	
е	_	_	0.35	
L	0.35	0.45	0.40	
K	0.15			
Z	_	_	0.065	
All Dimensions in mm				

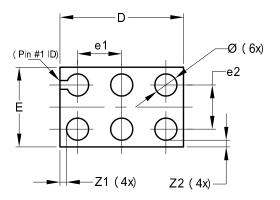


Dimensions	Value (in mm)	
С	0.350	
G	0.150	
Х	0.200	
X1	0.900	
Υ	0.550	
Y1	1.250	

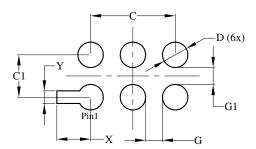


### X2-DFN1409-6 Package Outline Dimensions and Suggested Pad Layout





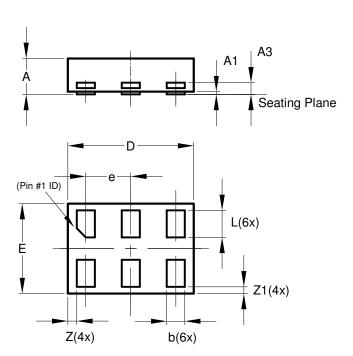
	X2-DFN1409-6				
Dim	Min	Max	Тур		
Α	-	0.40	0.39		
A1	0	0.05	0.02		
<b>A3</b>	-	1	0.13		
Ø	0.20	0.30	0.25		
D	1.35	1.45	1.40		
Е	0.85	0.95	0.90		
e1	-	-	0.50		
e2	-	-	0.50		
<b>Z</b> 1	-	-	0.075		
Z2	-	-	0.075		
All Dimensions in mm					



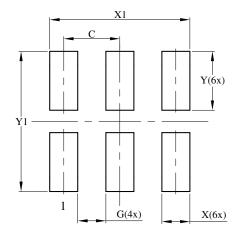
Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
X	0.400
Υ	0.150



### X2-DFN1410-6 Package Outline Dimensions and Suggested Pad Layout



X2-DFN1410-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A1	0.00	0.05	0.02	
A3		_	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е		_	0.50	
L	0.25	0.35	0.30	
Z		_	0.10	
<b>Z</b> 1	0.045	0.105	0.075	
All Dimensions in mm				



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
<b>X</b> 1	1.250
Y	0.525
Y1	1.250



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